

MC74VHC00

Quad 2-Input NAND Gate

The MC74VHC00 is an advanced high speed CMOS 2-input NAND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 3.7$ ns (Typ) at $V_{CC} = 5$ V
- Low Power Dissipation: $I_{CC} = 2$ μ A (Max) at $T_A = 25^\circ$ C
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\%$ V_{CC}
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8$ V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 32 FETs or 8 Equivalent Gates

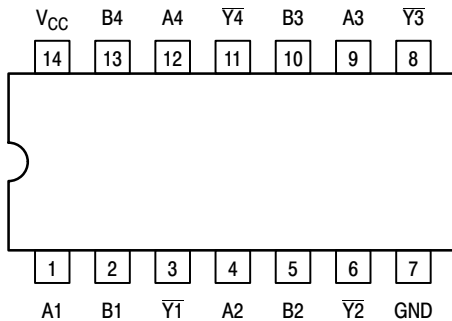


Figure 1. Pinout: 14-Lead Packages
(Top View)

FUNCTION TABLE

Inputs		Output
A	B	\bar{Y}
L	L	H
L	H	H
H	L	H
H	H	L

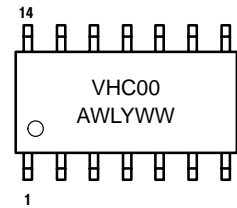


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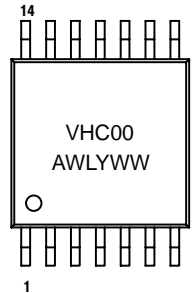
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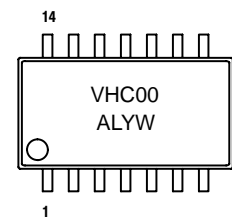

SO-14
D SUFFIX
CASE 751A-03




TSSOP-14
DT SUFFIX
CASE 948G-01




EIAJ SO-14
M SUFFIX
CASE 965-01



A = Assembly Location
L, WL = Wafer Lot
Y = Year
W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74VHC00DR2	SO-14	2500 Tape & Reel
MC74VHC00DT	TSSOP-14	96 Units/Rail
MC74VHC00DTR2	TSSOP-14	2500 Tape & Reel
MC74VHC00MEL	EIAJ SO-14	2000 Tape & Reel

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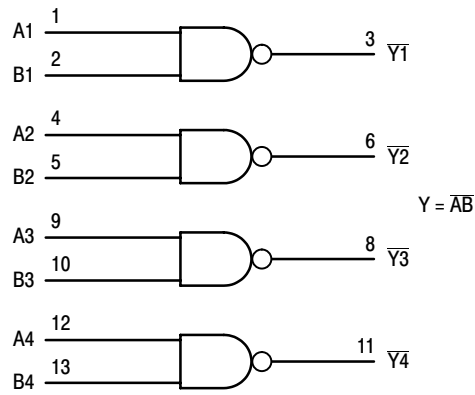


Figure 2. Logic Diagram

MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit	
V_{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V	
V_{IN}	Digital Input Voltage	-0.5 to +7.0	V	
V_{OUT}	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V	
I_{IK}	Input Diode Current	-20	mA	
I_{OK}	Output Diode Current	± 20	mA	
I_{OUT}	DC Output Current, per Pin	± 25	mA	
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 75	mA	
P_D	Power Dissipation in Still Air	SOIC Package 200 TSSOP 180	mW	
T_{STG}	Storage Temperature Range	-65 to +150	$^{\circ}C$	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) >2000 Machine Model (Note 3) >200 Charged Device Model (Note 4) N/A	V	
$I_{LATCH-UP}$	Latch-Up Performance	Above V_{CC} and Below GND at 125 $^{\circ}C$ (Note 5)	± 300	mA
θ_{JA}	Thermal Resistance, Junction to Ambient	SOIC Package 143 TSSOP 164	$^{\circ}C/W$	

1. Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.
2. Tested to EIA/JESD22-A114-A
3. Tested to EIA/JESD22-A115-A
4. Tested to JESD22-C101-A
5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	5.5	V
V_{IN}	DC Input Voltage	0	5.5	V
V_{OUT}	DC Output Voltage	0	V_{CC}	V
T_A	Operating Temperature Range, All Package Types	-55	125	$^{\circ}C$
t_r, t_f	Input Rise or Fall Time	$V_{CC} = 3.3 V \pm 0.3 V$ 0 $V_{CC} = 5.0 V \pm 0.5 V$ 0	100 20	ns/V

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = -40 to 85°C		T _A = -55 to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} × 0.7			1.50 V _{CC} × 0.7		1.50 V _{CC} × 0.7		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} × 0.3		0.50 V _{CC} × 0.3		0.50 V _{CC} × 0.3	V
V _{OH}	High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{OH} = - 50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V _{in} = V _{IH} or V _{IL} I _{OH} = - 4 mA I _{OH} = - 8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.40 3.70		
V _{OL}	Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V _{in} = V _{IH} or V _{IL} I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.55 0.55	
I _{in}	Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±2.0	μA
I _{CC}	Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			2.0		20		40	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A = -40 to 85°C		T _A = -55 to +125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, A or B to \bar{Y}	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF C _L = 50 pF		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0	1.0 1.0	10 14.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF		3.7 5.2	5.5 7.5	1.0 1.0	6.5 8.5	1.0 1.0	7.0 9.5	
C _{in}	Input Capacitance			4.0 10			10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 6)	Typical @ 25°C, V _{CC} = 5.0 V		pF
		19		

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0 ns, C_L = 50 pF, V_{CC} = 5.0 V, Measured in SOIC Package)

Symbol	Characteristic	T _A = 25°C		Unit
		Typ	Max	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.3	- 0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

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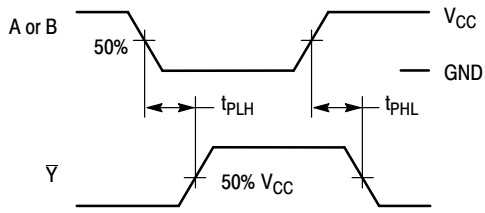
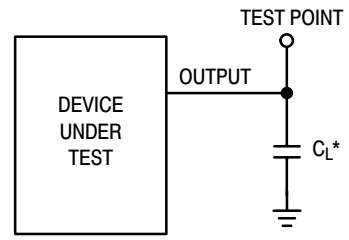


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

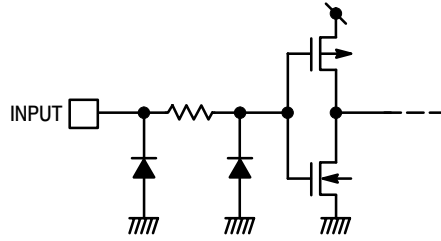
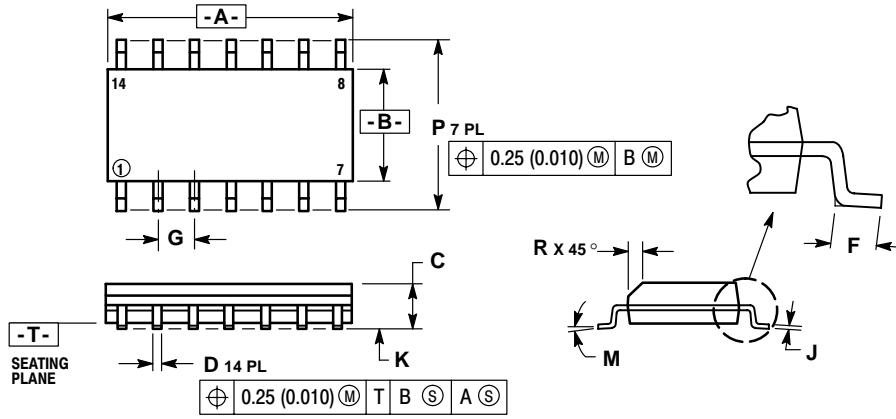


Figure 5. Input Equivalent Circuit

MC74VHC00

PACKAGE DIMENSIONS

SOIC-14
D SUFFIX
CASE 751A-03
ISSUE F



NOTES:

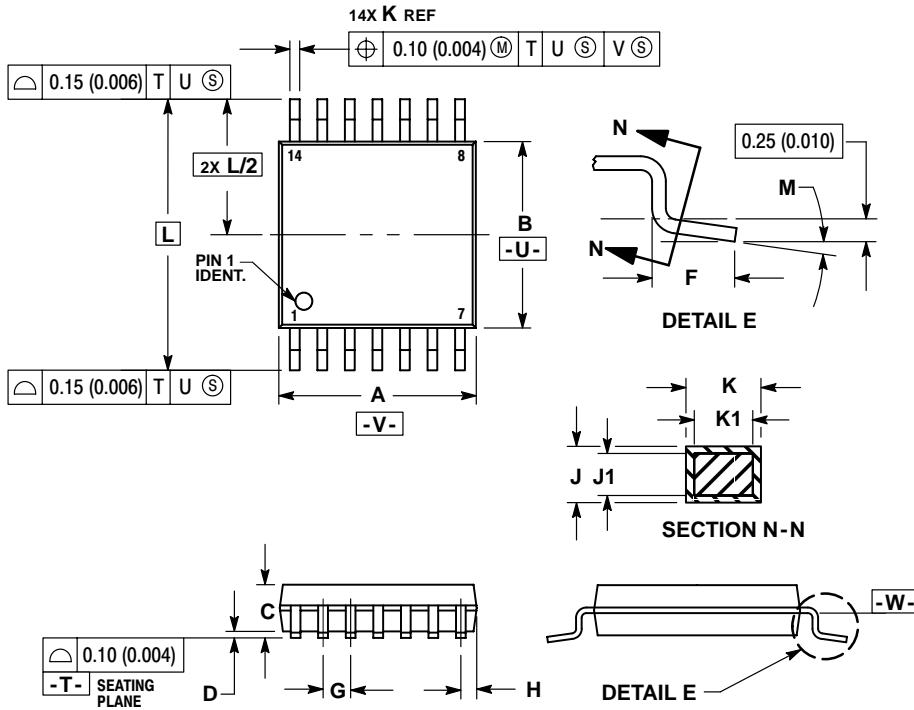
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2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

MC74VHC00

PACKAGE DIMENSIONS

TSSOP-14
DT SUFFIX
CASE 948G-01
ISSUE O



NOTES:

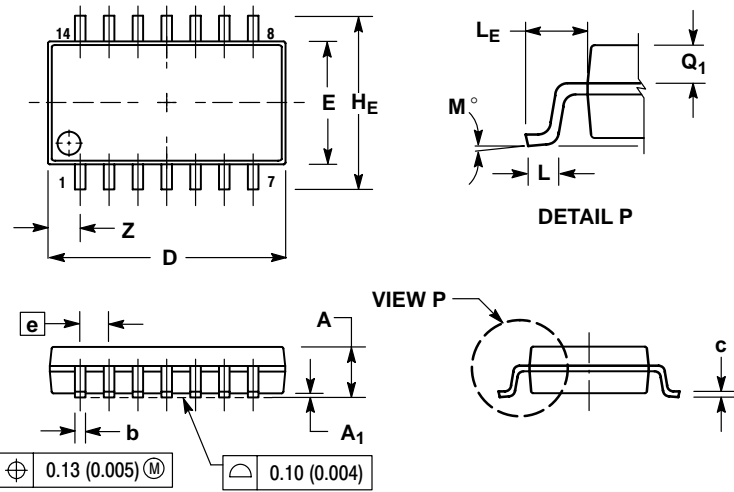
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -V-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

MC74VHC00

PACKAGE DIMENSIONS


SO-14
M SUFFIX
CASE 965-01
ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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